

OCT 25 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Jamal RAMDANI, et al.

SERIAL NO: 10/767,994

GAU: 2815

FILED: February 2, 2004

EXAMINER: BAUMEISTER

FOR: SEMICONDUCTOR STRUCTURE, SEMICONDUCTOR DEVICE, COMMUNICATING DEVICE, INTEGRATED CIRCUIT, AND PROCESS FOR FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, and copies were submitted in Application Serial No. 09/808,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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PATENT TRADEMARK OFFICE  
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SHEET 1 OF 23

Form PTO 1449 (Modified)  LIST OF REFERENCES CITED BY APPLICANT		ATTY DOCKET NO. 248402US99D		SHEET 1 OF 23	
		APPLICANT Jamal RAMDANI, et al.		SHEET 1 OF 23	
		FILING DATE February 2, 2004		GROUP 2815	
		U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
AA	3,802,967	04/09/74	Ladany et al.		
AB	4,174,422	11/13/79	Matthews et al.		
AC	4,404,265	09/13/83	Manasevit		
AD	4,482,906	11/13/84	Hovel et al.		
AE	4,523,211	06/11/85	Morimoto et al.		
AF	4,661,176	04/28/87	Manasevit		
AG	4,793,872	12/27/88	Meunier et al.		
AH	4,846,926	07/11/89	Kay et al.		
AJ	4,855,249	08/08/89	Akasaki et al.		
AI	4,891,091	01/02/90	Shastry		
AK	4,912,087	03/27/90	Aslam et al.		
AL	4,928,154	05/22/90	Umeno et al.		
AM	4,963,949	10/16/90	Wanlass et al.		
AN	5,141,894	08/25/92	Bisaro et al.		
AO	5,159,413	10/27/92	Calviello et al.		
AP	5,173,474	12/22/92	Connell et al.		
AQ	5,221,367	06/22/93	Chisholm et al.		
AR	5,225,031	07/06/93	McKee et al.		
AS	5,358,925	10/25/94	Neville Connell et al.		
AT	5,393,352	02/28/95	Summerfelt		
AU	5,418,216	05/23/95	Fork		
AV	5,450,812	09/19/95	McKee et al.		
AW	5,478,653	12/26/95	Guenzer		
AX	5,482,003	01/09/96	McKee et al.		
AY	5,514,484	05/07/96	Nashimoto		
AZ	5,556,463	09/17/96	Guenzer		
BA	5,588,995	12/31/96	Sheldon		
BB	5,670,798	09/23/97	Schetzina		
BC	5,733,641	03/31/98	Fork et al.		
BD	5,735,949	04/07/98	Mantl et al.		
BE	5,741,724	04/21/98	Ramdani et al.		
BF	5,810,923	09/22/98	Yano et al.		
BG	5,830,270	11/03/98	McKee et al.		
BH	5,912,068	06/15/99	Jia		
BI	6,020,222	02/01/00	Wollesen		
BJ	6,045,626	04/04/00	Yano et al.		
BK	6,064,078	05/16/00	Northrup et al.		
BL	6,064,092	05/16/00	Park		
BM	6,096,584	08/01/00	Ellis-Monaghan et al.		
BN	6,103,008	08/15/00	McKee et al.		
BO	6,136,666	10/24/00	So		
BP	6,174,755	01/16/01	Manning		
BQ	6,180,486	01/30/01	Leobandung et al.		

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LIST OF REFERENCES CITED BY APPLICANT			APPLICANT Jamal RAMDANI, et al.				
			FILING DATE February 2, 2004		GROUP 2815		
			<b>U.S. PATENT DOCUMENTS</b>				
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
CA	3,766,370	10/16/73	Walther				
CB	4,006,989	02/08/77	Andringa				
CC	4,284,329	08/18/81	Smith et al.				
CD	4,777,613	10/11/98	Shahan et al.				
CE	4,802,182	01/31/89	Thornton et al.				
CF	4,882,300	11/21/89	Inoue et al.				
CG	4,896,194	01/23/90	Suzuki				
CH	4,999,842	03/12/91	Huang et al.				
CI	5,081,062	01/14/92	Vasudev et al.				
CJ	5,155,658	10/13/92	Inam et al.				
CK	5,248,564	09/28/93	Ramesh				
CL	5,260,394	11/09/93	Tazaki et al.				
CM	5,270,298	12/14/93	Ramesh				
CN	5,286,985	02/15/94	Taddiken				
CO	5,310,707	05/10/94	Oishi et al.				
CP	5,326,721	07/05/94	Summerfelt				
CQ	5,404,581	04/04/95	Honjo				
CR	5,418,389	05/23/95	Watanabe				
CS	5,436,759	07/25/95	Dijaii et al.				
CT	5,576,879	11/19/96	Nashimoto				
CU	5,606,184	02/25/97	Abrokwah, et al.				
CV	5,640,267	06/17/97	May et al.				
CW	5,674,366	10/07/97	Hayashi et al.				
CX	5,729,641	03/17/98	Chandonnet et al.				
CY	5,790,583	08/04/98	Ho				
CZ	5,825,799	10/20/98	Ho et al.				
DA	5,857,049	01/05/99	Beranek et al.				
DB	5,874,860	02/23/99	Brunel et al.				
DG	5,926,496	07/20/99	Ho et al.				
DD	5,937,285	08/10/99	Abrokwah, et al.				
DE	5,981,400	11/09/99	Lo				
DF	5,990,495	11/23/99	Ohba				
DG	6,002,375	12/14/99	Corman et al.				
DH	6,008,762	12/28/99	Nghiem				
DI	6,055,179	04/25/00	Koganei et al.				
DJ	6,107,653	08/22/00	Fitzgerald				
DK	6,113,690	09/05/00	Yu et al.				
DL	6,114,996	09/05/00	Nghiem				
DM	6,121,642	09/19/00	Newns				
DN	6,128,178	10/03/00	Newns				
DO	6,143,072	11/07/00	McKee et al.				
DP	6,184,144	02/06/01	Lo				
DQ	6,222,654	04/24/01	Frigo				

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
EA	4,484,332	11/20/84	Hawrylo				
EB	4,815,084	03/21/89	Scifres et al.				
EC	4,876,219	10/24/89	Eshita et al.				
EO	4,963,508	10/16/90	Umeno et al.				
EF	5,060,031	10/22/91	Abrokwa, et al.				
EF	5,063,166	11/05/91	Mooney et al.				
EG	5,116,461	05/26/92	Lebby et al.				
EH	5,127,067	06/30/92	Delcoco et al.				
EI	5,144,409	09/01/92	Ma				
EJ	5,293,050	03/08/94	Chapple-Sokol et al				
EK	5,356,831	10/18/94	Calviello et al.				
EL	5,391,515	02/21/95	Kao et al.				
EM	5,442,191	08/15/95	Ma				
EN	5,444,016	08/22/95	Abrokwa, et al.				
EO	5,480,829	01/02/96	Abrokwa, et al.				
EP	5,528,414	06/18/96	Oakley				
EQ	5,614,739	03/25/97	Abrokwa et al.				
ER	5,729,394	03/17/98	Sevier et al.				
ES	5,731,220	03/24/98	Tsu et al.				
ET	5,764,676	06/09/98	Paoli et al.				
EU	5,777,762	07/07/98	Yamamoto				
EV	5,778,018	07/07/98	Yoshikawa et al.				
EW	5,778,116	07/07/98	Tomich				
EX	5,801,105	09/01/98	Yano et al.				
EY	5,828,080	10/27/98	Yano et al.				
EZ	5,858,814	01/12/99	Goossen et al.				
FA	5,861,966	01/19/99	Ortel				
FB	5,883,996	03/16/99	Knapp et al.				
FC	5,995,359	11/30/99	Klee et al.				
FD	6,058,131	05/02/00	Pan				
FE	6,137,603	10/24/00	Henmi				
FF	6,146,906	11/14/00	Inoue et al.				
FG	6,173,474	01/16/01	Conrad				
FH	6,180,252	01/30/01	Farrell et al.				
FI	4,242,595	12/30/0	Lehovec				
FJ	4,398,342	08/16/83	Pitt et al.				
FK	4,424,589	01/03/84	Thomas et al.				
FL	4,876,208	10/24/89	Gustafson et al.				
FM	4,482,422	11/84	McGinn et al.				
FN	4,667,088	05/19/87	Kramer				
FO	4,772,929	09/20/88	Manchester et al.				
FP	4,841,775	06/27/89	Ikeda et al.				
FQ	4,845,044	07/04/89	Ariyoshi et al.				

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GA		4,885,376	09/19/89	Lessin et al.			
GB		4,885,376	12/05/89	Verkade			
GC		4,888,202	12/90	Murakami et al.			
GD		4,891,091	12/90	Wanlass et al.			
GE		5,051,790	09/24/91	Hammer			
GF		5,055,445	10/08/91	Belt et al.			
GG		5,081,519	11/14/92	Nishimura et al.			
GH		5,143,854	09/01/92	Pirrung et al.			
GI		5,185,589	02/09/93	Krishnaswamy et al.			
GJ		5,191,625	03/02/93	Gustavsson			
GK		5,194,397	03/16/93	Cook et al.			
GL		5,208,182	05/04/93	Narayan et al.			
GM		5,216,729	06/01/93	Berger et al.			
GN		5,314,547	05/24/94	Heremans et al.			
GO		5,352,926	10/04/94	Andrews			
GP		5,356,509	10/18/94	Terranova et al.			
GQ		5,371,734	12/06/94	Fischer			
GR		5,372,992	12/94	Itozaki et al.			
GS		5,405,802	04/11/95	Yamagata et al.			
GT		5,442,561	08/15/95	Yoshizawa et al.			
GU		5,453,727	09/26/95	Shibasaki et al.			
GV		5,466,631	11/14/95	Ichikawa et al.			
GW		5,473,047	12/05/95	Shi			
GX		5,473,171	12/95	Summerfelt			
GY		5,479,033	12/26/95	Baca et al.			
GZ		5,486,406	01/23/96	Shi			
HA		5,491,461	02/13/96	Partin et al.			
HB		5,492,859	02/20/96	Sakaguchi et al.			
HC		5,494,711	02/27/96	Takeda et al.			
HD		5,504,035	04/02/96	Rostoker et al.			
HE		5,504,183	04/02/96	Shi			
HE		5,511,238	04/23/96	Bayraktaroglu			
HG		5,512,773	04/96	Wolf et al.			
HH		5,515,047	05/07/96	Yamakido et al.			
HI		5,515,810	05/14/96	Yamashita et al.			
HJ		5,519,235	05/96	Ramesh			
HK		5,549,977	08/96	Jin et al.			
HL		5,551,238	09/03/96	Prueitt			
HM		5,552,547	09/03/96	Shi			
HN		5,589,284	12/31/96	Summerfelt et al.			
HO		5,602,418	02/11/97	Imai et al.			
HP		5,633,724	05/27/97	King et al.			

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
IA	5,650,646	07/22/97	Summerfelt			
IB	5,656,382	08/12/97	Nashimoto			
IC	5,659,180	08/19/97	Shen et al.			
ID	5,661,112	08/26/97	Hatta et al.			
IE	5,679,965	11/95	Schetzina			
IF	5,725,641	03/10/98	MacLeod			
IG	5,745,631	04/28/98	Reinker			
IH	5,776,621	07/07/98	Nashimoto			
II	5,777,350	07/07/98	Nakamura et al.			
IJ	5,789,845	08/04/98	Wadaka et al.			
IK	5,792,569	08/11/98	Sun et al.			
IL	5,792,679	08/11/98	Nakato			
IM	5,796,648	08/18/98	Kawakubo et al.			
IN	5,801,072	09/01/98	Barber			
ID	5,812,272	09/22/98	King et al.			
IP	5,814,583	09/98	Itozaki et al.			
IQ	5,825,055	10/20/98	Summerfelt			
IR	5,827,755	10/27/98	Yonchara et al.			
IS	5,833,603	11/10/98	Kovacs et al.			
IT	5,838,035	11/17/98	Ramesh			
IU	5,844,260	12/01/98	Ohori			
IV	5,846,846	12/08/98	Suh et al.			
IW	5,863,326	01/26/99	Nause et al.			
IX	5,872,493	02/16/99	Ella			
IY	5,879,956	03/99	Seon et al.			
IZ	5,880,452	03/09/99	Plesko			
JA	5,883,564	03/16/99	Partin			
JB	5,907,792	05/25/99	Droopad et al.			
JC	5,937,274	08/10/99	Kondow et al.			
JD	5,948,161	09/07/99	Kizuki			
JE	5,959,879	09/28/99	Koo			
JF	5,966,323	10/99	Chen et al.			
JG	5,987,011	11/16/99	Toh			
JH	6,022,140	02/08/00	Fraden et al.			
JI	6,022,410	02/08/00	Yu et al.			
JJ	6,023,082	02/08/00	McKee et al.			
JK	6,028,853	02/22/00	Haartsen			
JL	6,049,702	04/11/00	Tham et al.			
JM	6,078,717	06/20/00	Nashimoto et al			
JN	6,088,216	07/00	Laibowitz et al.			
JO	6,090,659	07/00	Laibowitz et al.			
JP	6,107,721	08/22/00	Lakin			
JQ	6,153,010	11/28/00	Kiyoku et al			

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<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
KA		6,153,454	11/28/00	Krivokapic			
KB		6,191,011	02/01	Gilboa et al			
KC		6,204,737	03/20/01	Ella			
KD		6,224,669	05/01/01	Yi et al.			
KE		6,225,051	05/01/01	Sugiyama et al.			
KF		6,241,821	06/05/01	Yu et al.			
KG		6,265,749	07/24/01	Gardner et al.			
KH		6,313,486	11/01	Kencke et al.			
KI		6,316,832	11/13/01	Tsuzuki et al.			
KJ		2002/0008234	01/02	Emrick			
KK		3,670,213	06/13/72	Nakawaga et al.			
KL		4,756,007	07/05/88	Qureshi et al.			
KM		4,773,063	09/20/88	Hunsperger et al.			
KN		5,394,489	02/28/95	Koch			
KO		5,406,202	04/11/95	Mehrgardt et al.			
KP		5,528,067	06/18/96	Farb et al.			
KQ		5,572,052	11/05/96	Kashihara et al.			
KR		5,767,543	06/16/98	Ooms et al.			
KS		6,175,497	01/16/01	Tseng et al.			
KT		6,197,503	03/06/01	Vo-Dinh et al.			
KU		6,248,459	06/19/01	Wang et al.			
KV		6,252,261	06/26/01	Usui et al.			
KW		6,255,198	07/03/01	Linthicum et al.			
KX		6,268,269	07/31/01	Lee et al.			
KY		6,291,319	09/18/01	Yu et al.			
KZ		6,316,785	11/13/01	Nunoue et al.			
LA		6,343,171	01/29/02	Yoshimura et al.			
LB		4,965,649	10/23/90	Zanio et al.			
LC		6,253,649	05/01	Kawahara et al.			
LD		6,211,096	04/01	Allman et al.			
LE		6,239,449	05/29/01	Fafard et al.			
LF		2001/0013313	08/16/01	Droopad et al.			
LG		6,184,044	02/06/01	Sone et al.			
LH		6,011,646	01/04/00	Mirkarimi et al.			
LI		5,227,196	07/13/93	Itoh			
LJ		6,150,239	11/21/00	Goesele et al.			
LK		5,441,577	08/15/95	Sasaki et al.			
LL		4,459,325	07/10/84	Nozawa et al.			
LM		4,392,297	07/12/83	Little			
LN		4,289,920	09/15/81	Hovel			
LO		5,281,834	01/25/94	Cambou et al.			
LP		4,901,133	02/13/90	Curran et al.			
LQ		5,514,904	05/07/96	Onga et al.			

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U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	MA	5,553,089	09/03/96	Seki et al.				
	MB	5,528,057	06/18/96	Yanagase et al.				
	MC	6,229,159	05/08/01	Suzuki				
	MD	4,748,485	05/31/88	Vasudev				
	ME	4,984,043	01/08/91	Vinal				
	MF	5,754,319	05/19/98	Van De Voorde et al.				
	MG	6,108,125	08/22/00	Yano				
	MH	5,073,981	12/17/91	Giles et al.				
	MI	5,140,651	08/18/92	Soref et al.				
	MJ	5,610,744	03/11/97	Ho et al.				
	MK	6,362,017	03/26/02	Manabe et al.				
	ML	6,242,686	06/05/01	Kishimoto et al.				
	MM	5,689,123	11/18/97	Major et al.				
	MN	5,670,800	09/23/97	Nakao et al.				
	MO	5,067,809	11/26/91	Tsubota				
	MP	5,596,205	01/21/97	Reedy et al.				
	MQ	6,175,555	01/16/01	Hoole				
	MR	5,357,122	10/18/94	Okubora et al.				
	MS	4,084,130	04/11/78	Holton				
	MT	6,093,302	07/25/00	Montgomery				
	MU	6,372,813	04/16/02	Johnson et al.				
	MV	5,608,046	03/04/97	Cook et al.				
	MW	5,955,591	09/21/99	Imbach et al.				
	MX	6,022,963	02/08/00	McGall et al.				
	MY	6,083,697	07/04/00	Beecher et al.				
	MZ	5,063,081	11/05/91	Cozzette et al.				
	NA	5,479,317	12/26/95	Ramesh				
	NB	5,306,649	04/26/94	Hebert				
	NC	5,962,069	10/05/99	Schindler et al.				
	ND	5,541,422	07/30/96	Wolf et al.				
	NE	5,873,977	02/23/99	Desu et al.				
	NF	5,538,941	07/23/96	Findikoglu et al.				
	NG	6,046,464	04/04/00	Schetzina				
	NH	6,235,145	05/22/01	Li et al.				
	NI	5,610,744	03/11/97	Ho et al.				
	NJ	5,280,013	01/18/94	Newman et al.				
	NK	6,348,373 B1	02/19/02	Ma et al.				
	NL	6,339,664 B1	01/15/02	Farjady et al.				
	NM	4,439,014	03/27/84	Stacy et al.				
	NN	4,889,402	12/26/89	Reinhart				
	NO	5,963,291	10/05/99	Wu et al.				
	NP	6,011,641	01/04/00	Shin et al.				
	NQ	6,340,788 B1	01/22/02	King et al.				

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	OA	5,807,440	09/15/98	Kubota et al.	
	OB	4,681,982	07/21/87	Yoshida	
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.	
	OD	4,452,720	06/05/84	Harada et al.	
	OE	3,935,031	01/27/76	Adler	
	OF	5,760,426	06/02/98	Marx et al.	
	OG	5,053,835	10/01/91	Horikawa et al.	
	OH	6,326,645 B1	12/04/01	Kadota	
	OI	5,770,887	06/23/98	Tadatomo et al.	
	OJ	6,372,356 B1	04/16/02	Thornton et al.	
	OK	4,774,205	09/27/88	Choi et al.	
	OL	6,359,330 B1	03/19/02	Goudard	
	OM	5,312,765	05/17/94	Kanber	
	ON	5,734,672	03/31/98	McMinn et al.	
	OO	6,367,699 B2	04/09/02	Ackley	
	OP	5,530,235	06/25/96	Stefik et al.	
	OQ	5,623,552	04/22/97	Lane	
	OR	5,481,102	01/02/96	Hazelrigg, Jr.	
	OS	6,134,114	10/17/00	Ungermann et al.	
	OT	5,984,190	11/16/99	Nevill	
	OU	5,789,733	08/04/98	Jachimowicz et al.	
	OV	5,753,300	05/19/98	Wessels et al.	
	OW	6,208,453	03/27/01	Wessels et al.	
	OX	5,886,867	03/23/99	Chivukula et al.	
	OY	5,028,976	07/02/91	Ozaki et al.	
	OZ	5,869,845	02/09/99	Vander Wagt et al.	
	PA	5,596,214	01/21/97	Endo	
	PB	6,391,674 B2	05/21/02	Ziegler	
	PC	6,275,122 B1	08/14/01	Speidell et al.	
	PD	6,238,946 B1	05/29/01	Ziegler	
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	PF	6,392,257	05/21/02	Ramdani et al.	
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	PH	5,603,764	02/18/97	Matsuda et al.	
	PI	6,087,681	06/11/00	Shakuda	
	PJ	5,132,648	07/21/92	Trinh et al.	
	PK	6,427,066	07/30/02	Grube	
	PL	2002/0072245	06/13/02	Ooms et al.	
	PM	6,278,138 B1	08/21/01	Suzuki	
	PN	5,888,296	03/30/99	Ooms et al.	
	PO	5,198,269	03/30/93	Swartz et al.	
	PP	2002/0030246	03/14/02	Eisenbeiser et al.	
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	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
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	QU	5,334,556	08/02/94	Guldi			
	QV	4,910,164	03/20/90	Shichijo			
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	RJ	5,753,928	05/19/98	Krause			
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	RL	5,130,762	07/14/92	Kulick			
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	RN	6,389,209 B1	05/14/02	Suhir			
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	SB	5,395,663	03/07/95	Tabata et al.				
	SC	4,146,297	03/27/79	Alfernness et al.				
	SD	5,452,118	09/19/95	Maruska				
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	SY	4,120,588	10/17/78	Chaum				
	SZ	5,194,917	03/16/93	Regener				
	TA	5,018,816	05/28/91	Murray et al.				
	TB	5,953,468	09/14/99	Finnila et al.				
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	TJ	5,668,048	09/16/97	Kondo et al.				
	TK	5,852,687	12/22/98	Wickham				
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	UC	6,297,842 B1	10/02/01	Koizumi et al.				
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	UG	6,013,553	01/11/00	Wallace et al.				
	UH	4,872,046	10/03/89	Morkoc et al.				
	UI	2002/0047123 A1	04/25/02	Ramdani et al.				
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	UN	5,373,166	12/13/94	Buchan et al.				
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	UQ	4,981,714	01/01/91	Ohno et al.				
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	US	6,326,637 B1	12/04/01	Parkin et al.				
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	UV							
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	UX							
	UY							
	UZ							
	VA							
	VB							
	VC							
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	VM							
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	VP							
	VQ							

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					YES      NO
	AAA	0 250 171	12/23/87	EP	X
	AAB	0 342 937	11/23/89	EP	X
	AAC	0 455 526	06/11/91	EP	X
	AAD	0 602 568	06/22/94	EP	X
	AAE	0 607 435	07/27/94	EP	X
	AAF	1 001 468	05/17/00	EP	X
	AAG	0 514 018	11/19/92	EP	X
	AAH	0 999 600	05/10/00	EP	X
	AAI	1 319 311	06/04/70	Great Britain	X
	AAJ	5-291299	11/05/93	Japan w/English Abstract	X
	AAK	11-238683	08/31/99	Japan	X
	AAL	11-260835	09/24/99	Japan w/English Abstract	X
	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X
	AAN	5-48072	02/26/93	Japan w/English Abstract	X
	AAO	52-88354	07/23/77	Japan w/English Abstract	X
	AAP	54-134554	10/19/79	Japan w/English Abstract	X
	AAQ	55-87424	07/02/80	Japan w/English Abstract	X
	AAR	61-108187	05/26/86	Japan w/English Abstract	X
	AAS	6-232126	08/19/94	Japan	X
	AAT	6-291299	10/18/94	Japan w/English Abstract	X
	AAU	63-34994	02/15/88	Japan w/English Abstract	X
	AAV	63-131104	06/03/88	Japan w/English Abstract	X
	AAW	63-198365	08/17/88	Japan w/English Abstract	X
	AAX	10-321943	12/04/98	Japan	X
	AAY	6-334168	12/02/94	Japan	X
	AAZ	WO 99/63580	12/09/99	WIPO	X
	ABA	WO 99/14804	03/25/99	WIPO	X
	ABB	WO 97/45827	12/04/97	WIPO	
	ABC	WO 99/19546	04/22/99	WIPO	
	ABD	WO 00/33363	06/08/00	WIPO	
	ABE	WO 00/48239	08/17/00	WIPO	
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	ABH	1 109 212	06/20/01	Europe	
	ABI	DE 197 12 496	10/30/97	Germany	X
	ABJ	60-212018	10/24/85	Japan w/English Abstract	
	ABK	60-210018	10/22/85	Japan w/English Abstract	
	ABL	WO 92/10875	06/25/92	WIPO	
	ABM	0 682 266	11/15/95	Europe	
	ABN	3-41783	02/91	Japan (English Abstract only)	
	ABO	0 581 239	02/02/94	Europe	
	ABP	0812494	01/16/96	Japan	
	ABQ	2 000 1645	06/16/00	Japan	

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BAA	1 043 426	10/11/00	Europe		
BAB	2000-068466	03/00	Japan (Abstract)		
BAC	64-50575	02/27/89	Japan		
BAO	WO 98/05807	01/12/98	WIPO		
BAE	WO 94/03908	02/17/94	WIPO		
BAF	WO 01/33585	05/10/01	WIPO		
BAG	1-102435	04/20/89	Japan w/English Abstract		
BAH	52-135684	11/12/77	Japan (English Abstract)		
BAI	02051220	02/21/90	Japan (English Abstract)		
BAJ	11135614	05/21/99	Japan (w/English Abstract)		
BAK	64-52329	02/28/89	Japan (w/English Abstract)		
BAL	10-256154	09/25/98	Japan (w/English Abstract)		
BAM	DE 196 07 107	08/28/97	Germany		xx
BAN	10-303396	11/13/98	Japan (w/English Abstract)		
BAO	58-213412	12/12/83	Japan w/English Abstract		
BAP	0 964 259	12/15/99	Europe		
BAQ	0 875 922	11/04/98	Europe		
BAR	61-63015	04/01/86	Japan w/English Abstract		
BAS	11340542	12/10/99	Japan (English Abstract)		
BAT	WO 01/37330	05/25/01	WIPO		
BAU	0 331 467	09/06/89	Europe		
BAV	WO 00/16378	03/23/00	WIPO		
BAW	0 926 739	06/30/99	Europe		
BAX	0 964 453	12/15/99	Europe		
BAY	5-152529	06/18/93	Japan w/English Abstract		
BAZ	9-67193	03/11/97	Japan w/English Abstract		
BBA	9-82913	03/28/97	Japan w/English Abstract		
BBB	0 309 270	03/29/89	Europe		
BBC	EP 0 957 522	11/17/99	Europe		
BBD	EP 0 810 666	12/03/97	Europe		
BBE	1-179411	07/17/89	Japan w/English Abstract		
BBF	DE 100 17 137	10/26/00	GERMANY		
BBG	WO 02 01648	01/03/02	WIPO		
BBH	WO 02/33385 A2	04/25/02	WIPO		
BBI	WO 01/59814 A2	08/16/01	WIPO		
BBJ	WO 02/09160 A2	01/31/02	WIPO		
BBK	WO 00/06812	02/10/00	WIPO		
BBL	0 483 993	05/06/92	Europe		
BBM	0 538 611	04/28/93	Europe		
BBN	WO 01/59820 A1	08/16/01	WIPO		
BBO	05150143	06/18/93	Japan (English Abstract only)		
BBP	2 779 843	12/17/99	France		xx
BBQ	5-086477	04/06/93	Japan (English Abstract only)		

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CAA	52-89070		07/26/77	Japan	xx
CAB	EP 1 069 606		01/17/01	Europe	
CAC	WO 02/03113		01/10/02	WIPO	
CAD	WO 02/03467		01/10/02	WIPO	
CAE	0 630 057		12/21/94	EUROPE	
CAF	61-36981		02/21/86	Japan w/English Abstract	
CAG	WO 93/07647		04/15/93	WIPO	
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CAI	EP 0 881 669		12/02/98	Europe	
CAJ	WO 02/03480		01/10/02	WIPO	
CAK	WO 02/50879		06/27/02	WIPO	
CAL	EP 0 777 379		06/04/97	Europe	
CAM	WO 01/04943 A1		01/18/01	WIPO	xx
CAN	WO 02/47127 A2		06/13/02	WIPO	
CAO	JP 58-075868		05/07/83	Japan w/English Abstract	
CAP	EP 0 993 027		04/12/00	Europe	
CAQ	EP 0 711 853		05/15/96	Europe	
CAR	WO 98/20606		05/14/98	WIPO	
CAS	EP 1 043 765		10/11/00	Europe	
CAT	0 300 499		01/25/89	Europe	
CAU	EP 1 085 319		03/21/01	Europe	
CAV	WO 01/16395		03/08/01	WIPO	
CAW	2000-351692		12/19/00	Japan w/English Abstract	
CAX	03-188619		08/16/91	Japan (English Abstract only)	
CAY	63-289812		11/28/88	Japan (English Abstract only)	
CAZ	EP 0 884 767		12/16/98	Europe	
CBA	06-069490		03/11/94	Japan (English Abstract only)	
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CBE					
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CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.				
CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", <i>1998 Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.				
CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.				
CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO <sub>3</sub> Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.				
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IIA Q	Hideaki Adachi et al.; "Sputtering Preparation of Ferroelectric PLZT Thin Films and Their Optical Applications"; IEEE Transactions of Ultrasonics, Ferroelectrics and Frequency Control, Vol. 38, No. 6, November 1991

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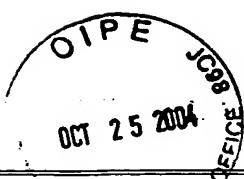
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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Jamal RAMDANI, et al.	
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<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>					
JJAA	A.J. Moulson et al.; "Electroceramics Materials Properties Applications"; Chapman & Hall; pp. 366-369				
JJAB	P.A. Langjahr et al.; "Epitaxial Growth and Structure of Cubic and Pseudocubic Perovskite Films on Perovskite Substrates"; Mat. Res. Soc. Symp. Proc., Vol. 401; 1995 Materials Research Society; pp. 109-114				
JJAC	Wang et al.; "Depletion-Mode GaAs MOSFETs with Negligible Drain Current Drift and Hysteresis"; Electron Devices Meeting, 1998, IEDM '98 Technical Digest; pp. 67-70				
JJAD	Ben G. Streetman; "Solid State Electronic Devices"; 1990, Prentice Hall; Third Edition; pp. 320-322				
JJAE	A.Y Wu et al.; "Highly Oriented (Pb,La)(Zr,Ti)O <sub>3</sub> Thin Films on Amorphous Substrates"; IEEE, 1992; pp. 301-304				
JJAC	Timothy E. Glassman et al.; "Evidence for Cooperative Oxidation of MoCVD Precursors Used in Ba <sub>x</sub> Sr <sub>1-x</sub> TiO <sub>3</sub> Film Growth"; Mat. Res. Soc. Symp. Proc. Vol. 446, 1997 Materials Research Society; pp. 321-326				
JJAG	S.N. Subbarao et al.; "Monolithic PIN Photodetector and FET Amplifier on GaAs-os-Si"; IEEE; GaAs IC Symposium-163-166; 1989				
JJAH	T.A. Langdo et al.; "High Quality Ge on Si by Epitaxial Necking"; Applied Physics Letters; Vol. 76, No. 25; pp. 3700-3702; June 19, 2000				
JJAI	Chenning Hu et al.; Solar Cells From Basics to Advanced Systems; McGraw-Hill Book Company; 1983				
JJAJ	O.J. Painter et al; "Room Temperature Photonic Crystal Defect Lasers at Near-Infrared Wavelengths in InGaAsP"; Journal of Lightwave Technology, Vol. 17, No. 11; November 1999				
JJAK	C. Donn et al.; "A 16-Element, K-Band Monolithic Active Receive Phased Array Antenna"; Antennas and Propagation Society International Symposium, 1988; pp.188-191, Vol. 1; 6-10 June 1988				
JJAL	Don W. Shaw; "Epitaxial GaAs on Si: Progress and Potential Applications"; Mat. Res. Soc. Symp. Proc.; pp.15-30; 1987				
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JJAN	P.J. Borrelli et al.; "Compositional and Structural Properties of Sputtered PLZT Thin Films"; Ferroelectric Thin Films II Symposium; Dec. 2-4, 1991 (Abstract)				
JJAO	Ranu Nayak et al; "Enhanced acousto-optic diffraction efficiency in a symmetric SrTiO <sub>3</sub> /BaTiO <sub>3</sub> /SrTiO <sub>3</sub> thin-film heterostructure"; 1 November 2000; Vol. 39, No. 31; Applied Optics; pp. 5847-5853				
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KKAB	Katherine Derbyshire; "Prospects Bright for Optoelectronics Volume, Cost Drive Manufacturing for Optical Applications"; Semiconductor Magazine; Vol. 3, No. 3; March 2002			
KKAC	Alex Chediak et al; "Integration of GaAs/Si with Buffer Layers and Its Impact on Device Integration"; TICS 4, Prof. Sands. MSE 225, April 12, 2002; pp. 1-5			
KKAD	S.A. Chambers et al; "Band Discontinuities at Epitaxial SrTiO <sub>3</sub> /Si(001) Heterojunctions"; Applied Physics Letters; Vol. 77, No. 11; September 11, 2000; pp. 1662-1664			
KKAI	H. Wang et al.; "GaAs/GaAlAs Power HBTs for Mobile Communications"; Microwave Symposium Digest; 1993 IEEE; Vol. 2.; pp. 549-552			
KKAF	Y. Ota et al.; "Application of Heterojunction FET to Power Amplifier for Cellular Telephone"; Electronics Letters; 26th May 1994; Vol. 30, No. 11; pp. 906-907			
KKAG	Keiichi Sakuno et al; "A 3.5W HBT MMIC Power Amplifier Module for Mobile Communications"; IEEE 1994; Microwave and Millimeter-Wave Monolithic Circuits Symposium; pp. 63-66			
KKAH	Mitsubishi Semiconductors Press Release (GaAs FET's) November 8, 1999 pp.1-2			
KKAI	R.J. Matyi et al; "Selected Area Heteroepitaxial Growth of GaAs on Silicon for Advanced Device Structures"; 2194 Thin Solid Films; 181 (1989) December 10; No. 1; pp. 213-225			
KKAJ	K. Nashimoto et al; "Patterning of Nb, LaOnZr, TiO <sub>3</sub> Waveguides for Fabricating Micro-Optics Using Wet Etching and Solid-Phase Epitaxy"; Applied Physics Letters; Vol. 75, No. 8; 23 August 1999; pp. 1054-1056			
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KKAL	Man Fai Ng et al; "Heteroepitaxial growth of lanthanum aluminate films derived from mixed metal nitrates"; Journal of Materials Research; Vol. 12, No. 5; pp. 1306			
KKAM	Yuji Matsumoto et al.; "Room-Temperature Ferromagnetism in Transparent Transition Metal-Doped Titanium Dioxide"; Science; 2 February 2001; Vol. 291; pp. 854-856			
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KKAO				
KKAP				
KKAQ				
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	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
	VD	6,198,119 B1	03/06/01	Nabatame et al.			
	VE	6,113,225	09/05/00	Miyata et al.			
	VF	5,262,659	11/16/93	Grudkowski et al.			
	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
	VK	6,080,378	06/27/00	Yokota et al.			
	VL	5,508,554	04/16/96	Takatani et al.			
	VM	6,477,285 B1	11/05/02	Shanley			
	VN	4,695,120	09/22/87	Holder			
	VO	5,882,948	03/16/99	Jewell			
	VP	5,574,589	11/12/96	Feuer et al.			
	VQ	5,510,665	04/23/96	Conley			
	VR	4,804,866	02/14/89	Akiyama			
	VS	5,057,694	10/15/91	Idaka et al.			
	VT	5,635,453	06/03/97	Pique et al.			
	VU	5,719,417	02/17/98	Roeder et al.			
	VV	5,998,819	12/07/99	Yokoyama et al.			
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
VW	2002/0079576	06/27/02	Seshan		
VX	5,148,504	09/15/92	Levi et al.		
VY	2002/0195610 A1	12/26/02	Klosowiak		
VZ	5,477,363	12/19/95	Matsuda		
WA	5,905,571	05/18/99	Butler et al.		
WB	5,570,226	10/29/96	Ota		
WC	5,087,829	02/11/92	Ishibashi et al.		
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WE	6,496,469 B1	12/17/02	Uchizaki		
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WH	5,446,719	08/29/95	Yoshida et al.		
WI	5,831,960	11/03/98	Jiang et al.		
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WU	5,362,972	11/08/94	Yazawa et al.		
WV	5,864,171	01/26/99	Yamamoto et al.		
WW	5,028,563	07/02/91	Feit et al.		
WX	5,937,115	08/10/99	Domash		
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	WY	5,878,175	03/02/99	Sonoda et al.			
	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
	XD	5,772,758	06/30/98	Collins et al.			
	XE	5,666,376	09/09/97	Cheng			
	XF	5,976,953	11/02/99	Zavracky et al.			
	XG	5,578,162	11/26/96	D'Asaro et al.			
	XH	5,585,167	12/17/96	Satoh et al.			
	XI	5,674,813	10/07/97	Nakamura et al.			
	XJ	5,574,296	11/12/96	Park et al.			
	XK	6,504,189	01/07/03	Matsuda et al.			
	XL	5,987,196	11/16/99	Noble			
	XM						
	XN						
	XO						
	XP						
	XQ						
	XR						
	XS						
	XT						
	XU						
	XV						
	XW						
	XX						
	XY						
	XZ						
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FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES                    NO
	CBC	EP 1 035 759	09/13/00	Europe	
	CBD	EP 0 860 913	08/26/95	EUROPE	
	CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT	
	CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT	
	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT	
	CBH	EP 1 089 338	04/04/01	EUROPE	
	CBI	01 294594	11/28/99	JAPAN (ABSTRACT)	
	CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)	
	CBK	03-149882	11/07/89	JAPAN	
	CBL	0 614 256	09/07/94	EUROPE	
	CBM	1 054 442	11/22/00	EUROPE	
	CBN	0 852 416	07/08/98	EUROPE	
	CBO	W0 02/08806	01/31/02	WIPO	
	CBP	W0 01/59837	08/16/01	WIPO	
	CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT	
	CBR	0 600 658	06/08/94	EUROPE	
	CBS	0 412 002	02/06/91	EUROPE	
	CBT	2000-349278	12/15/00	JAPAN (ENGLISH ABSTRACT)	
	CBU	01-196809	08/08/89	JAPAN (ENGLISH ABSTRACT)	
	CBV	0 619 283	10/12/94	EUROPE	
	CBW	0 661 561	07/05/95	EUROPE	
	CBX	0 331 338	09/06/89	EUROPE	
	CBY				
	CBZ				
	CCA				
	CCB				
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	CCG				
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<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>				
KKAO	Charles Kittel; "Introduction to Solid State Physics"; John Wiley & Sons, Inc. Fifth Edition; pp. 415			
KKAP	Chyuan-Wei Chen et al; "Liquid-phase epitaxial growth and characterization of InGaAsP layers grown on GaAsP substrates for application to orange light-emitting diodes"; 931 Journal of Applied Physics; 77 (1995) 15 January, No. 2; Woodbury, NY, US; pp. 905-909			
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KKAR	M. Schreck et al.; "Diamond/Ir/SrTiO <sub>3</sub> : A material combination for improved heteroepitaxial diamond films"; Applied Physics Letters; Vol. 74, No. 5; February 1, 1999; pp. 650-652			
KKAS	Yoshihiro Yokota et al.; "Cathodoluminescence of boron-doped heteroepitaxial diamond films on platinum"; Diamond and Related Materials 8(1999); pp. 1587-1591			
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KKAX	L. Fan et al.; "Dynamic Beam Switching of Vertical-Cavity Surface-Emitting Lasers with Integrated Optical Beam Routers"; IEEE Photonics Technology Letters; Vol. 9, No. 4; April 4, 1997; pp. 505-507			
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KKAZ	Kiyoko Kato et al.; "Reduction of dislocations in InGaAs layer on GaAs using epitaxial lateral overgrowth"; 2300 Journal of Crystal Growth 115 (1991) pp. 174-179; December 1991			
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	XN	6,233,435 B1	05/15/01	WONG			
	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
	XU	6,232,242 B1	05/15/01	HATA ET AL			
	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
	XY	4,298,247	11/03/81	MICHELET ET AL			
	XZ	4,174,504	11/13/79	CHENAUSKY ET AL			
	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
	YF	2002/0179000 A1	12/05/02	LEE ET AL			
	YG	6,341,851	01/29/02	TAKAYAMA ET AL			
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	YJ	5,985,404	11/16/99	YANO ET AL			
	YK	6,538,359 B1	03/25/03	HIRAKU ET AL			
	YL	6,498,358 B1	12/24/02	LACH ET AL			
	YM	5,387,811	02/07/95	SAIGOH			
	YN	5,523,602	06/04/96	HORIUCHI ET AL			
	YO	5,362,998	11/08/94	IWAMURA ET AL			
	YP	5,188,976	02/23/93	KUME ET AL			
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	YQ	6,501,121 B1	12/31/02	YU ET AL			
	YR	5,919,515	07/06/99	YANO ET AL			
	YS	5,238,877	08/24/93	RUSSELL			
	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL			
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		FOREIGN PATENT DOCUMENTS				
	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
				YES	NO	
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CCB	2 152 315	07/31/85	GREAT BRITAIN			
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CCE	WO 03/012874	02/13/03	WIPO			
CCF	1 043 427	10/11/00	EUROPE			
CCG	1 069 605	01/17/01	EUROPE			
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LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001		
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LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO <sub>3</sub> Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651		
LLAF	V. Bornand et al.; "Deposition of LiTaO <sub>3</sub> thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244		
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	A6	6,329,277	12/11/01	LIU ET AL			
	A7						
	A8						
	A9						
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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
	CCS	WO 99/67882	12/29/99	WIPO			
	CCT	WO 95/02904	01/26/95	WIPO			
	CCU	WO 02/009150	01/31/02	WIPO			
	CCV	0 766 292	04/02/97	EUROPE			
	CCW	198 29 609	01/05/00	GERMANY			
	CCX	1 069 605	01/17/01	EUROPE			
	CCY	0 828 287	03/11/98	EUROPE			
	CCZ	1 176 230	01/30/02	EUROPE			
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
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LLAR							
LLAS					<input type="checkbox"/> Additional References sheet(s) attached		
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